

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Hiroshi TOBIMATSU, ct al.

Serial No.: 09/910,824

Filed: July 24, 2001 /

Group Art Unit: 2812

Examiner: LEE, Hsien Ming

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE HAVING

PASSIVATION FILM AND BUFFER COATING FILM

<u>AMENDMENT</u>

Commissioner for Patents Washington, DC 20231

Sir:

For:

The following Amendment and Remarks are submitted in response to the Office Action dated January 14, 2003.

IN THE CLAIMS:

Please amend claim 1 as follows.

(Amended) A method of manufacturing a semiconductor device 1. comprising the steps of:

forming an interconnection on a semiconductor substrate having a semiconductor element formed thereon;

forming a passivation film on the semiconductor substrate including the interconnection;